

# BCW66GLT1G, SBCW66GLT1G

## General Purpose Transistor

### NPN Silicon

#### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

| Rating                         | Symbol    | Value | Unit |
|--------------------------------|-----------|-------|------|
| Collector–Emitter Voltage      | $V_{CEO}$ | 45    | Vdc  |
| Collector–Base Voltage         | $V_{CBO}$ | 75    | Vdc  |
| Emitter–Base Voltage           | $V_{EBO}$ | 5.0   | Vdc  |
| Collector Current – Continuous | $I_C$     | 800   | mAdc |
| Collector Current – Pulsed     | $I_C$     | 1200  | mAdc |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

| Characteristic                                                                                                      | Symbol          | Max         | Unit                       |
|---------------------------------------------------------------------------------------------------------------------|-----------------|-------------|----------------------------|
| Total Device Dissipation FR–5 Board<br>(Note 1), $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$        | $P_D$           | 225<br>1.8  | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction–to–Ambient                                                                          | $R_{\theta JA}$ | 556         | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation Alumina<br>Substrate, (Note 2) $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$           | 300<br>2.4  | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction–to–Ambient                                                                          | $R_{\theta JA}$ | 417         | $^\circ\text{C}/\text{W}$  |
| Junction and Storage Temperature                                                                                    | $T_J, T_{stg}$  | –55 to +150 | $^\circ\text{C}$           |

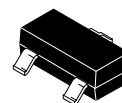
1. FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

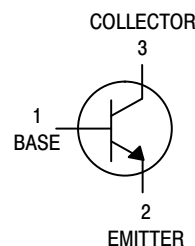


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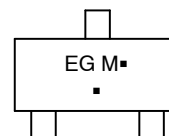
<http://onsemi.com>



SOT-23  
(TO-236)  
CASE 318-08  
STYLE 6



#### MARKING DIAGRAM



EG = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(\*Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

| Device      | Package             | Shipping†          |
|-------------|---------------------|--------------------|
| BCW66GLT1G  | SOT-23<br>(Pb-Free) | 3,000/Tape & Reel  |
| SBCW66GLT1G | SOT-23<br>(Pb-Free) | 3,000/Tape & Reel  |
| BCW66GLT3G  | SOT-23<br>(Pb-Free) | 10,000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                                                                              |               |        |        |          |                         |
|----------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|--------|----------|-------------------------|
| Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )                                                                     | $V_{(BR)CEO}$ | 45     | –      | –        | Vdc                     |
| Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $V_{EB} = 0$ )                                                         | $V_{(BR)CES}$ | 75     | –      | –        | Vdc                     |
| Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )                                                                 | $V_{(BR)EBO}$ | 5.0    | –      | –        | Vdc                     |
| Collector Cutoff Current<br>( $V_{CE} = 45\text{ Vdc}$ , $I_E = 0$ )<br>( $V_{CE} = 45\text{ Vdc}$ , $I_E = 0$ , $T_A = 150^\circ\text{C}$ ) | $I_{CES}$     | –<br>– | –<br>– | 20<br>20 | nAdc<br>$\mu\text{Adc}$ |
| Emitter Cutoff Current ( $V_{EB} = 4.0\text{ Vdc}$ , $I_C = 0$ )                                                                             | $I_{EBO}$     | –      | –      | 20       | nAdc                    |

### ON CHARACTERISTICS

|                                                                                                                                                                                                                                                            |               |                        |                  |                    |     |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|------------------------|------------------|--------------------|-----|
| DC Current Gain<br>( $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 10\text{ Vdc}$ )<br>( $I_C = 10\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )<br>( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )<br>( $I_C = 500\text{ mA}$ , $V_{CE} = 2.0\text{ Vdc}$ ) | $h_{FE}$      | 50<br>110<br>160<br>60 | –<br>–<br>–<br>– | –<br>–<br>400<br>– | –   |
| Collector–Emitter Saturation Voltage<br>( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )<br>( $I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$ )                                                                                                               | $V_{CE(sat)}$ | –<br>–                 | –<br>–           | 0.7<br>0.3         | Vdc |
| Base–Emitter Saturation Voltage<br>( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )                                                                                                                                                                        | $V_{BE(sat)}$ | –                      | –                | 2.0                | Vdc |

### SMALL-SIGNAL CHARACTERISTICS

|                                                                                                                                                  |           |     |   |    |     |
|--------------------------------------------------------------------------------------------------------------------------------------------------|-----------|-----|---|----|-----|
| Current–Gain — Bandwidth Product<br>( $I_C = 20\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 100\text{ MHz}$ )                                   | $f_T$     | 100 | – | –  | MHz |
| Output Capacitance<br>( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )                                                            | $C_{obo}$ | –   | – | 12 | pF  |
| Input Capacitance<br>( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )                                                            | $C_{ibo}$ | –   | – | 80 | pF  |
| Noise Figure<br>( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 0.2\text{ mA}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ ) | NF        | –   | – | 10 | dB  |

### SWITCHING CHARACTERISTICS

|                                                                     |           |   |   |     |    |
|---------------------------------------------------------------------|-----------|---|---|-----|----|
| Turn–On Time ( $I_{B1} = I_{B2} = 15\text{ mA}$ )                   | $t_{on}$  | – | – | 100 | ns |
| Turn–Off Time ( $I_C = 150\text{ mA}$ , $R_L = 150\text{ }\Omega$ ) | $t_{off}$ | – | – | 400 | ns |

## TYPICAL CHARACTERISTICS

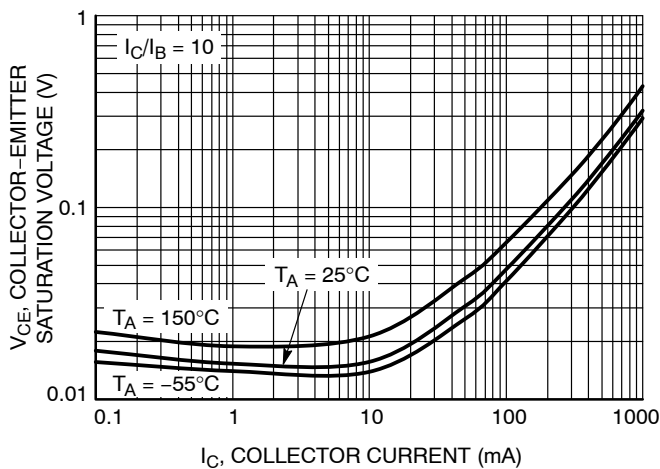


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

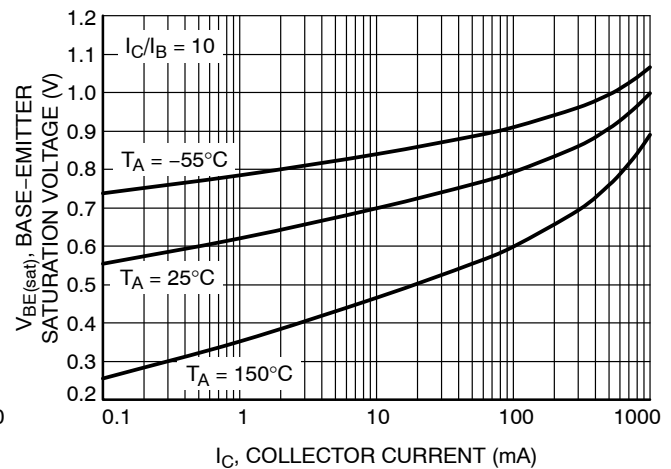
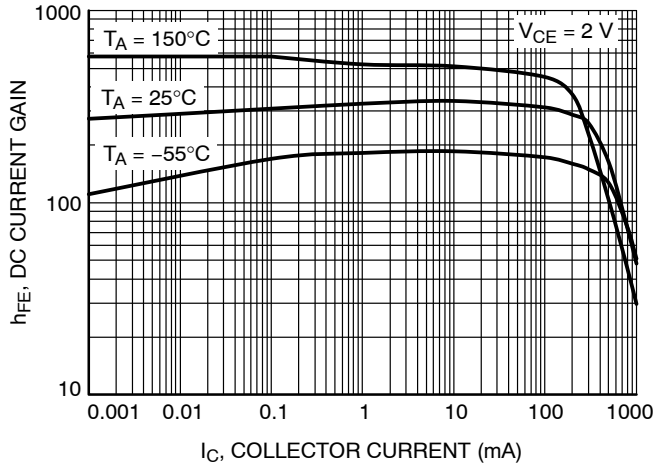


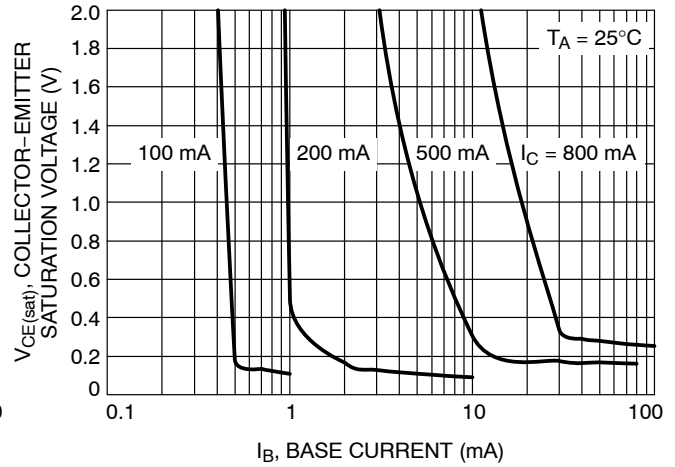
Figure 2. Base Emitter Saturation Voltage vs. Collector Current

# BCW66GLT1G, SBCW66GLT1G

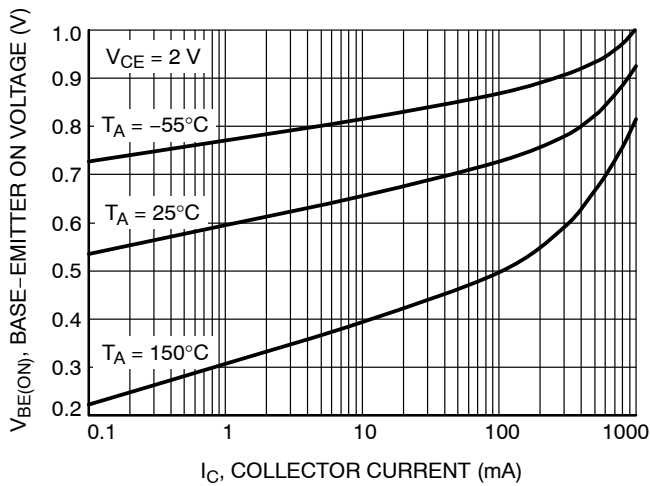
## TYPICAL CHARACTERISTICS



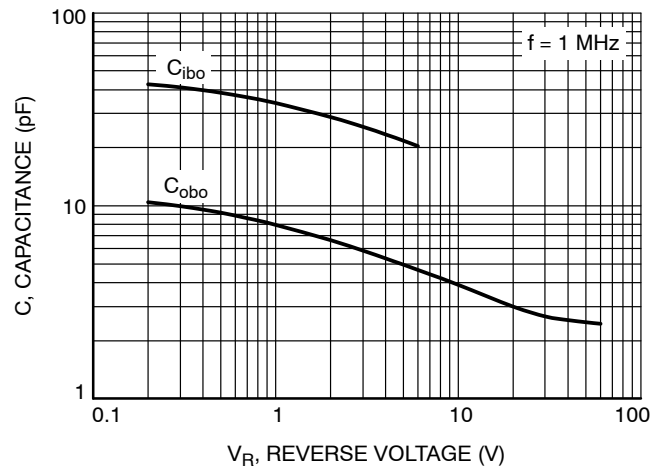
**Figure 3. DC Current Gain vs. Collector Current**



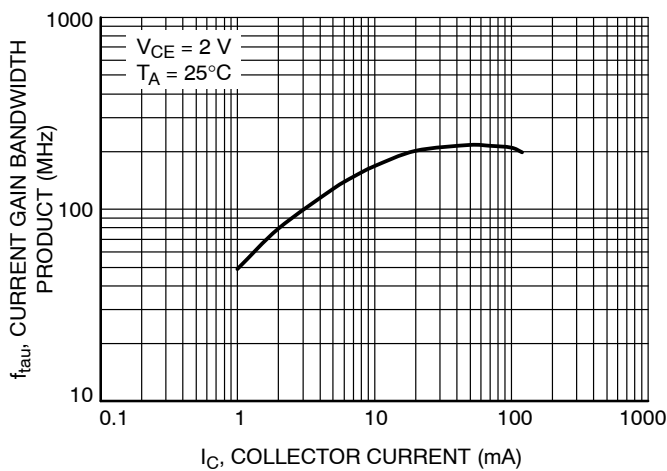
**Figure 4. Saturation Region**



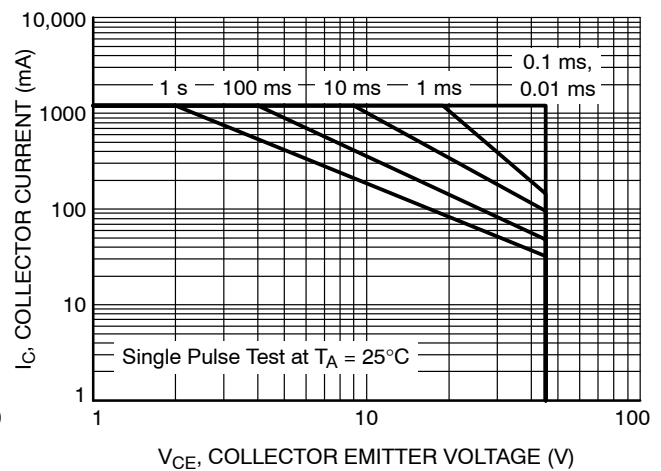
**Figure 5. Base-Emitter Turn-On Voltage vs. Collector Current**



**Figure 6. Capacitance**



**Figure 7. Current Gain Bandwidth Product vs. Collector Current**

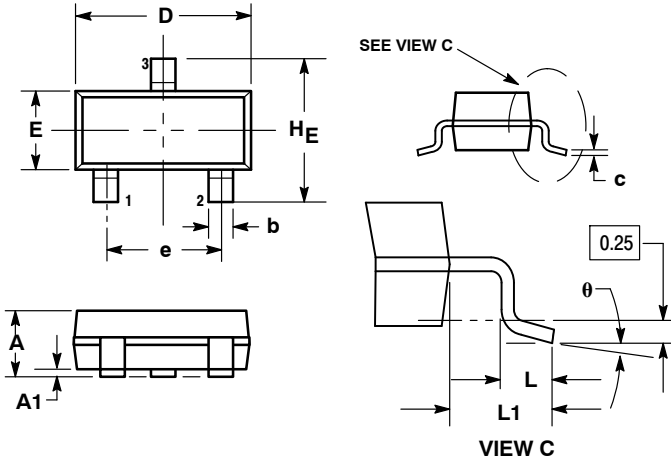


**Figure 8. Safe Operating Area**

# BCW66GLT1G, SBCW66GLT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP



### NOTES:

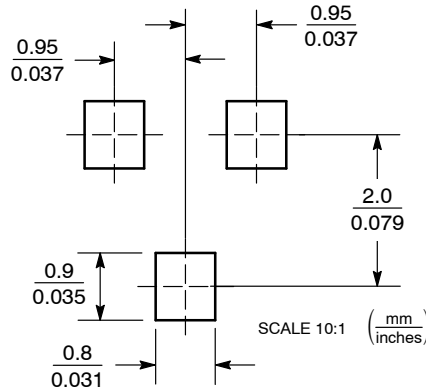
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 0.89        | 1.00 | 1.11 | 0.035  | 0.040 | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015  | 0.018 | 0.020 |
| c   | 0.09        | 0.13 | 0.18 | 0.003  | 0.005 | 0.007 |
| D   | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E   | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| e   | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.081 |
| L   | 0.10        | 0.20 | 0.30 | 0.004  | 0.008 | 0.012 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.029 |
| H_E | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| θ   | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

### STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

## SOLDERING FOOTPRINT



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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А